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(Use several sheets if necessary)

IONESCU et al

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IONESCU et al
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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS		FILING DATE IF APPROPRIATE
				CLASS	SUBCLASS	
BS	4,906,586	3/1990	Blackburn	438	53	
BS	5,262,000	11/1993	Welbourn et al	156	643	
BS	6,290,864	9/2001	Patel et al	216	79	

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

<p>P1</p>	Ionescu et al, "Modeling and Design of a Low-Voltage SOI Suspended-Gate MOSFET (SG-MOSFET) with a Metal-Over-Gate Architecture", PROCEEDINGS OF THE 2002 3 RD INTERNATIONAL SYMPOSIUM ON QUALITY ELECTRONIC DESIGN, March 18-21, 2002, pp. 496-501.
<p>P2</p>	Hoffman et al, "3D Structures with Piezoresistive Sensors in Standard CMOS", PROCEEDINGS OF THE WORKSHOP ON MICRO ELECTRICAL MECHANICAL SYSTEMS", January 29 - February 2, 1995, pp. 288-293.
<p>P3</p>	Devoe et al, "Surface Micromachined Piezoelectric Accelerometers (PIXLS)", JOURNAL OF MICROELECTROMECHANICAL SYSTEMS, IEEE INC., vol. 10, no. 2, June 2001, pp. 180-186.
<p>P4</p>	Chang et al, "Innovative micromachined microwave switch with very low insertion loss", SENSORS AND ACTUATORS A, ELSEVIER SEQUOIA S.A., LAUSANNE, CH, vol. 79, no. 1, January 2000, pp. 71-75.
<p>P5</p>	Pott et al, "The suspended-gate MOSFET (SG-MOSFET): a modeling outlook for the design of RF MEMS switches and tunable capacitors", 2001 INTERNATIONAL SEMICONDUCTOR CONFERENCE, CAS 2001 PROCEEDINGS (CAT. NO. 01TH8547), CAS 2001 PROCEEDINGS. 2001 INTERNATIONAL SEMICONDUCTOR CONFERENCE, SINAIA, ROMANIA, 9-13 Oct. 2001, pp. 137-140.
<p>P6</p>	Zhang et al, "Temperature-controlled Kelvin microprobe", SENSORS AND ACTUATORS B, ELSEVIER SEQUOIA S.A., LAUSANNE, CH, vol. B12, no. 3, 15 April 1993, pp. 175-180.
<p>P7</p>	Meister et al, "In situ control of the electrochemical gap height modification of a suspended gate field-effect transistor by capacitance -- voltage measurement technique", SENSORS AND ACTUATORS B, ELSEVIER SEQUOIA S.A., LAUSANNE, CH, vol. 46, no. 3, 15 May 1998, pp. 226-235.

***Examiner**

Date Considered

7/10/06

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